

IGBT MODULE (N series)

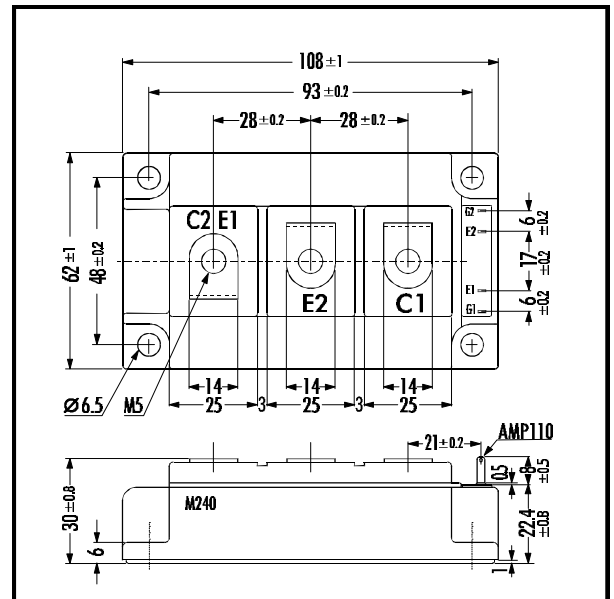
■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (4~5 Times Rated Current)

■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

■ Outline Drawing



■ Maximum Ratings and Characteristics

• Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	1200	V
Gate -Emitter Voltage	V_{GES}	± 20	V
Collector Current	Continuous	I_C	100
	1ms	$I_{C \text{ PULSE}}$	200
	Continuous	$-I_C$	100
	1ms	$-I_{C \text{ PULSE}}$	200
Max. Power Dissipation	P_C	780	W
Operating Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +125	$^\circ\text{C}$
Isolation Voltage	A.C. 1min.	V_{is}	2500
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	

Note: *1:Recommendable Value; 2.5 ~ 3.5 Nm (M5) or (M6)
*2:Recommendable Value; 3.5 ~ 4.5 Nm (M6)

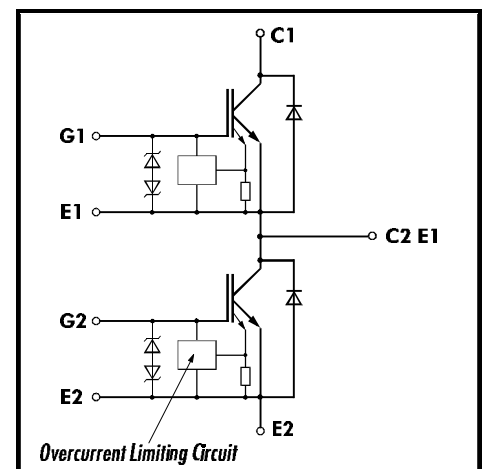
• Electrical Characteristics (at $T_j=25^\circ\text{C}$)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0V$ $V_{CE}=1200V$			2.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V$ $V_{GE}=\pm 20V$			30	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=20V$ $I_C=100\text{mA}$	4.5		7.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V$ $I_C=100A$			3.3	V
Input capacitance	C_{ies}	$V_{GE}=0V$		16000		pF
Output capacitance	C_{oes}	$V_{CE}=10V$		5800		
Reverse Transfer capacitance	C_{res}	$f=1\text{MHz}$		5160		
Turn-on Time	t_{ON}	$V_{CC}=600V$		0.65	1.2	μs
	t_r	$I_C=100A$		0.25	0.6	
Turn-off Time	t_{OFF}	$V_{GE}=\pm 15V$		0.85	1.5	
	t_f	$R_G=9.1\Omega$		0.35	0.5	
Diode Forward On-Voltage	V_F	$I_F=100A$ $V_{GE}=0V$			3.0	V
Reverse Recovery Time	t_{rr}	$I_F=100A$			350	ns

• Thermal Characteristics

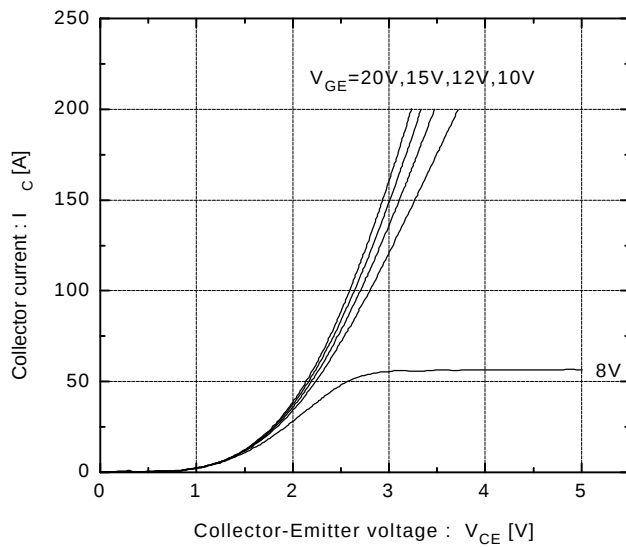
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.16	$^\circ\text{C/W}$
	$R_{th(j-e)}$	Diode			0.43	
	$R_{th(c-f)}$	With Thermal Compound		0.025		

■ Equivalent Circuit



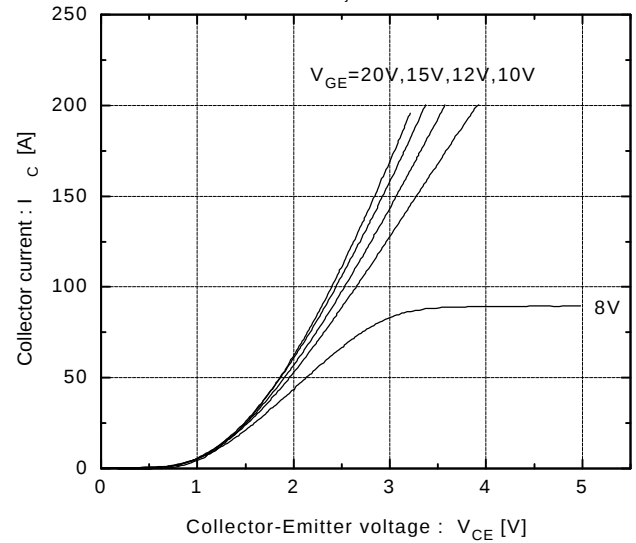
Collector current vs. Collector-Emitter voltage

$T_J=25^\circ\text{C}$



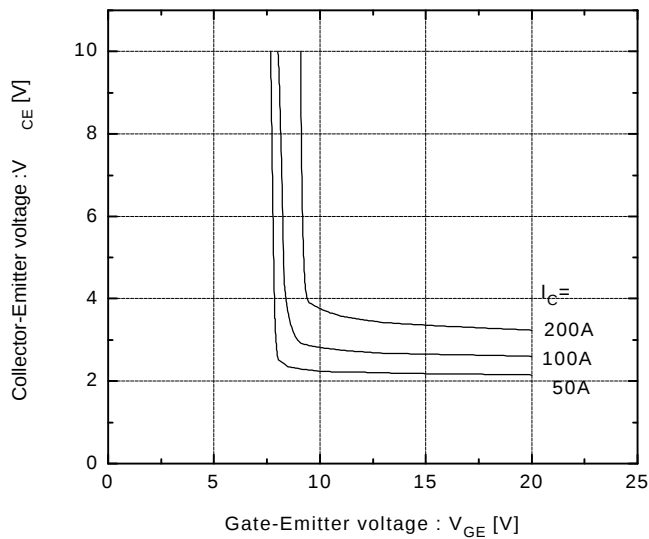
Collector current vs. Collector-Emitter voltage

$T_J=125^\circ\text{C}$



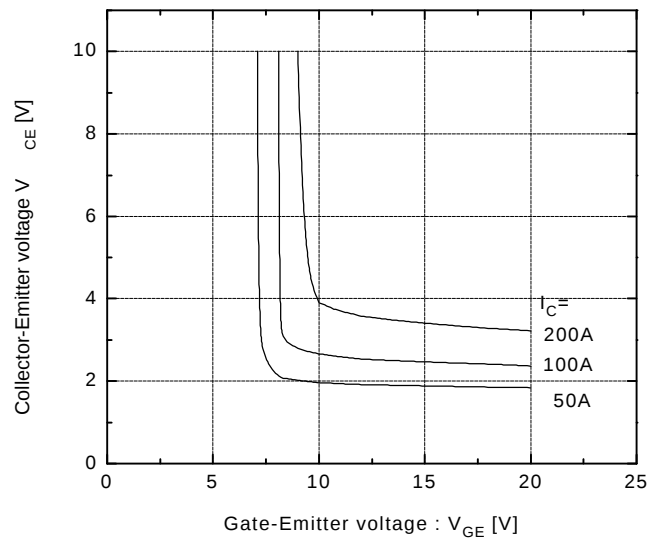
Collector-Emitter vs. Gate-Emitter voltage

$T_J=25^\circ\text{C}$

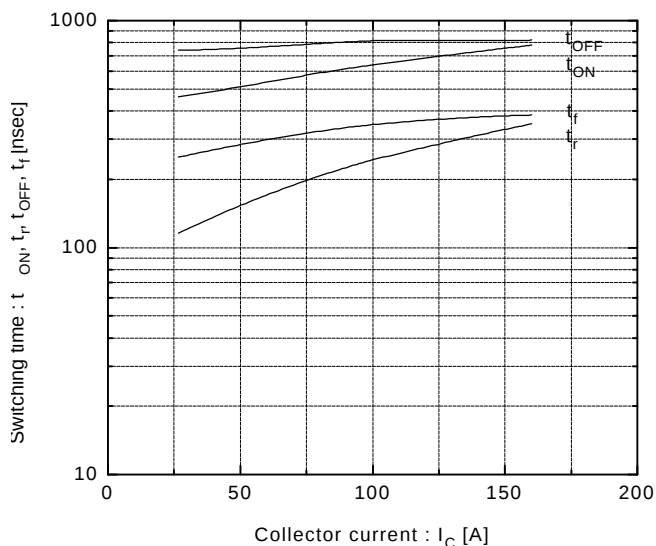


Collector-Emitter vs. Gate-Emitter voltage

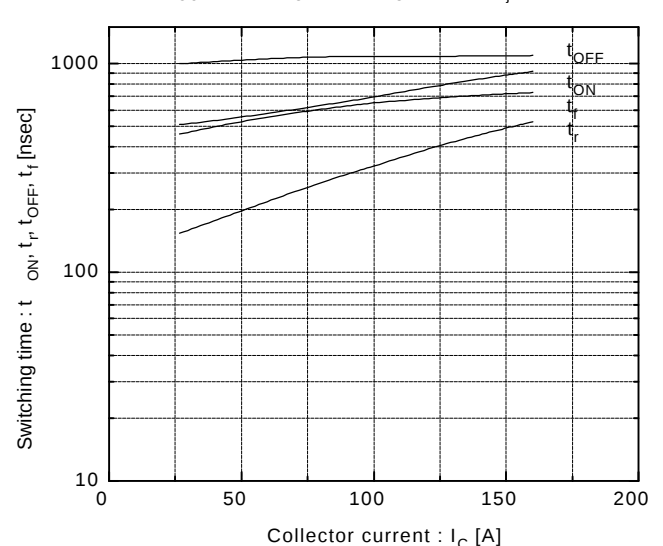
$T_J=125^\circ\text{C}$



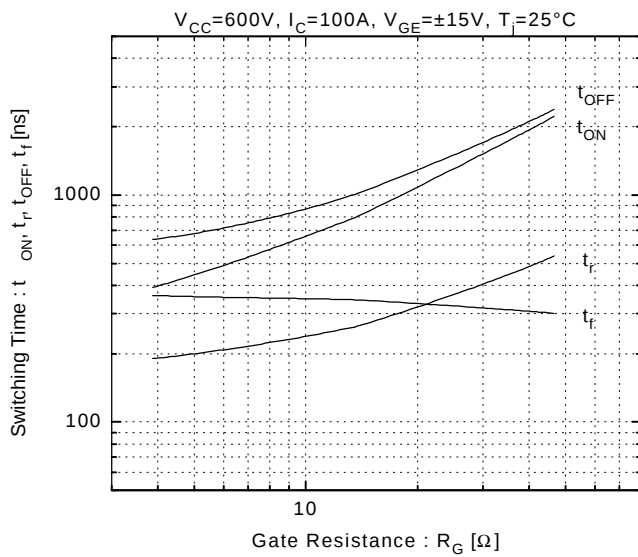
Switching time vs. Collector current
 $V_{CC}=600\text{V}, R_G=9.1\Omega, V_{GE}=\pm 15\text{V}, T_J=25^\circ\text{C}$



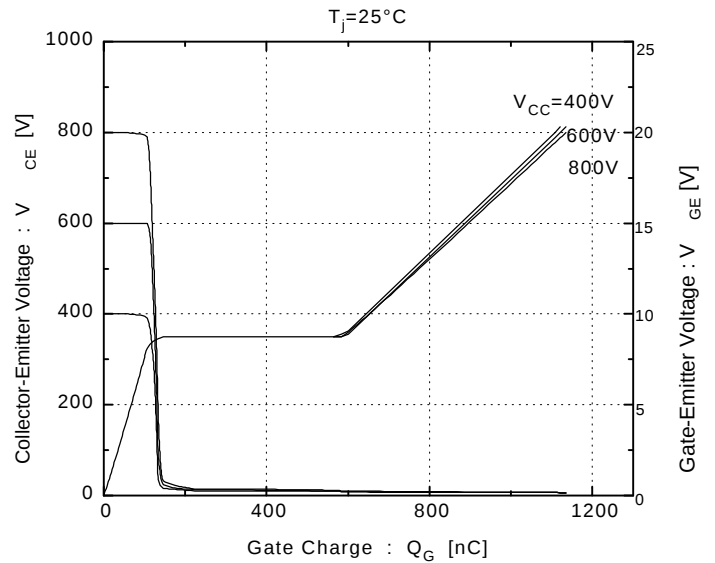
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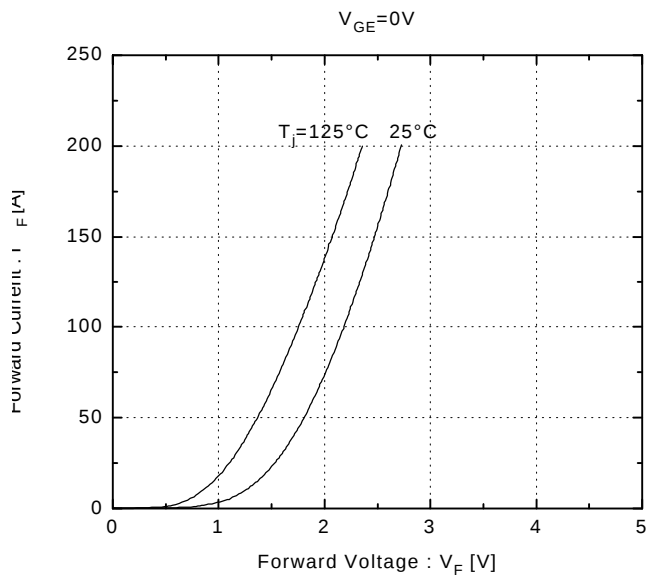
Switching Time vs. R_G



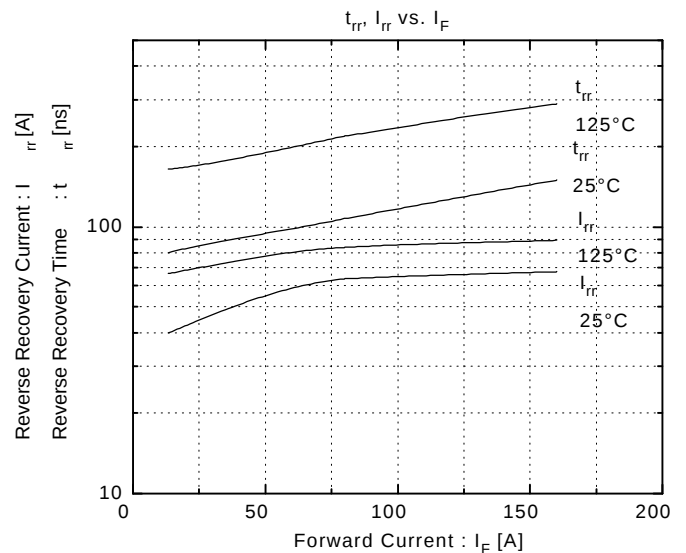
Dynamic Input Characteristics



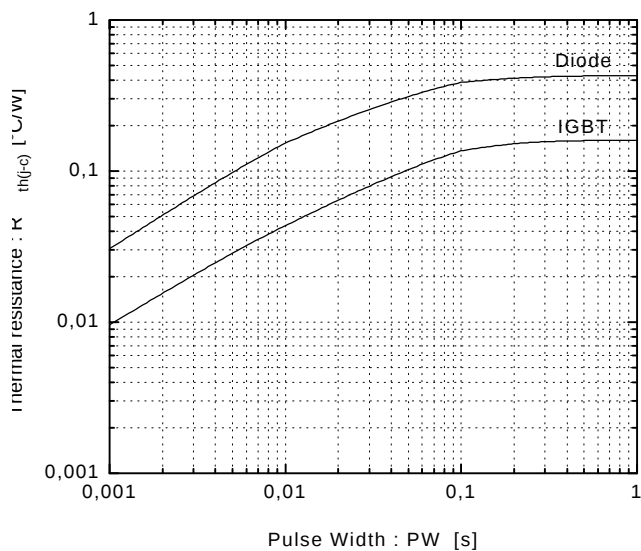
Forward Current vs. Forward Voltage



Reverse Recovery Characteristics

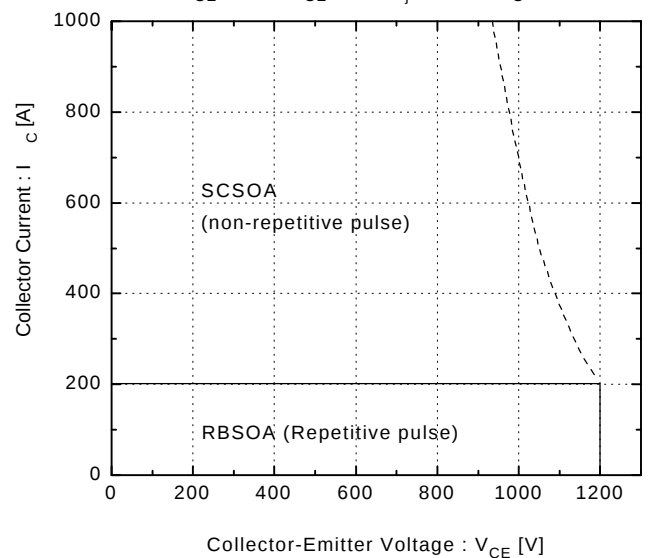


Transient Thermal Resistance

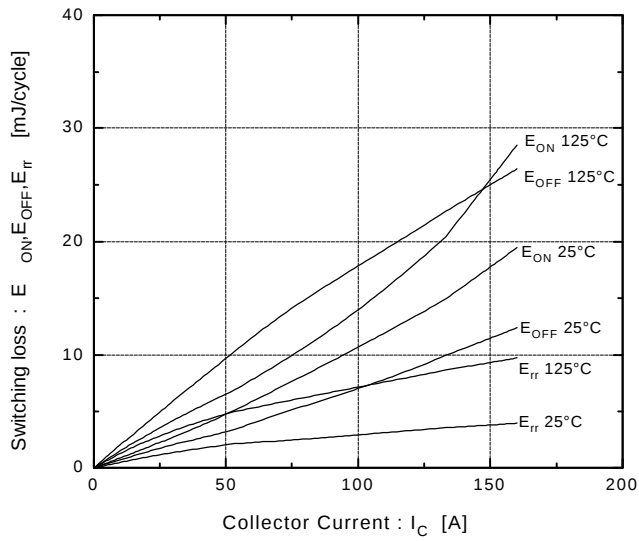


Reversed Biased Safe Operating Area

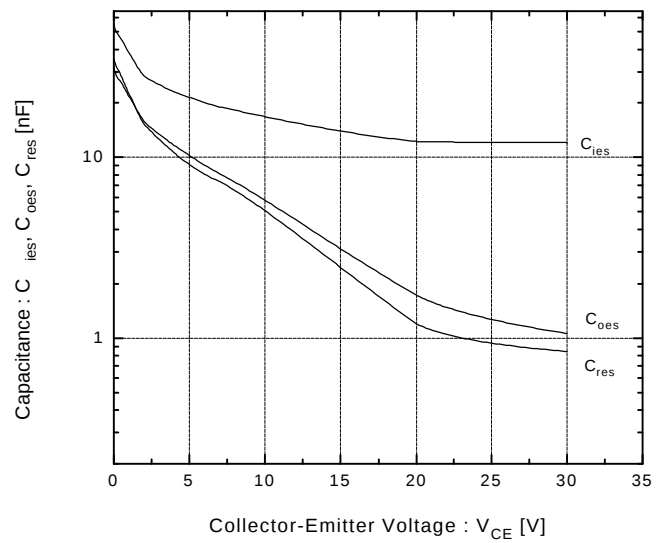
$+V_{GE}=15V, -V_{GE}\leq 15V, T_J\leq 125^\circ C, R_G\geq 9.1\Omega$



Switching loss vs. Collector current

 $V_{CC}=600V$, $R_G=9.1\Omega$, $V_{GE}=\pm 15V$


Capacitance vs. Collector-Emitter voltage

 $T_J=25^\circ C$

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